IN THE CLAIMS

1.	(cancelled)
2.	(cancelled)
3.	(cancelled)
4.	(cancelled)
5.	(cancelled)
6.	(cancelled)
7.	(cancelled)
8.	(cancelled)
9.	(cancelled)
10.	(cancelled)
11	(cancelled)

- 12. (cancelled)
- 13. (cancelled)
- 14. (cancelled)
- 15. (cancelled)
- 16. (cancelled)
- 17. (cancelled)
- 18. (previously presented) The method of claim 21 wherein the desired temperature coefficient of resistance is about zero.
- 19. (previously presented) The method of claim 21 wherein the resistor is formed as a part of a standard CMOS process flow.
- 20. (cancelled)

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- 21. (previously presented) A method for fabricating a resistor having a desired temperature coefficient of resistance and a total electrical resistance, the method comprising the steps of forming a polysilicon layer having:
 - a first unsilicided resistor segment having a first electrical resistance and a negative temperature coefficient of resistance, and
 - a second silicided resistor segment having a second electrical resistance and a positive temperature coefficient of resistance, the second segment electrically connected in series with the first segment,
 - where the second electrical resistance is related to the first electrical resistance according to:

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$$\frac{R_1}{R_2} = \left| \frac{TCR_2}{TCR_1} \right|,$$

where R_1 is the first electrical resistance of the first resistor segment,

 R_2 is the second electrical resistance of the second resistor segment,

TCR₁ is the negative temperature coefficient of resistance of the first resistor segment, and

TCR₂ is the positive temperature coefficient of resistance of the second resistor segment.

- 22. (previously presented) The method of claim 21 wherein at least one of the first unsilicided resistor segment and the second silicided resistor segment is formed to be substantially rectangular.
- 23. (previously presented) The method of claim 21 wherein at least one of the first unsilicided resistor segment and the second silicided resistor segment is formed to be substantially serpentine.
- 24. (previously presented) The method of claim 21 wherein the total electrical resistance R_T is determined by:

$$R_T = R_2 \times \left(\left| \frac{TCR_2}{TCR_1} \right| + 1 \right).$$

where R_T is the total electrical resistance of the resistor,

5 R₂ is the second electrical resistance of the second unsilicided resistor segment,

TCR₁ is the temperature coefficient of resistance of the first silicided resistor segment, and

TCR₂ is the temperature coefficient of resistance of the second unsilicided resistor segment.